



STGW40NC60WD

N-channel 40A - 600V - TO-247
Very fast switching PowerMESH™ IGBT

General features

Type	V _{CE(S)}	V _{CE(sat)} (Max)@ 25°C	I _C @100°C
STGW40NC60WD	600V	<2.5V	40A

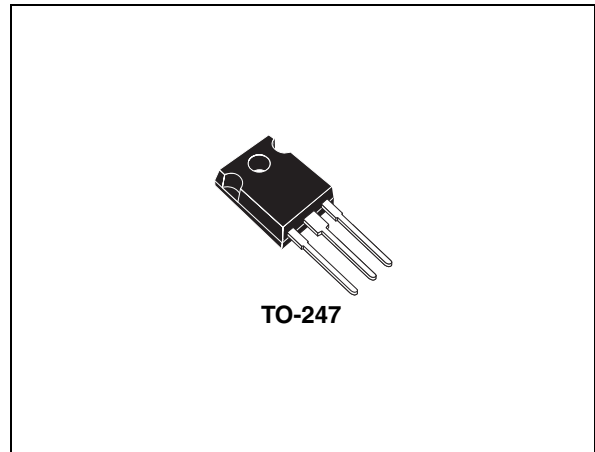
- Low C_{RES} / C_{IES} ratio (no cross conduction susceptibility)
- High frequency operation
- Very soft ultra fast recovery anti parallel diode

Description

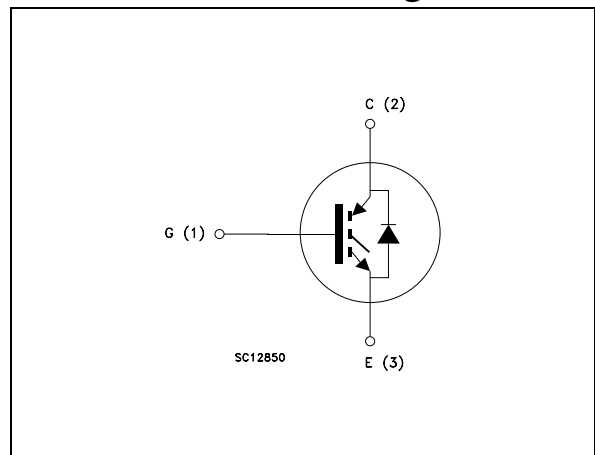
Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix “W” identifies a family optimized for very high frequency application.

Applications

- High frequency inverters, UPS
- Motor drivers
- HF, SMPS and PFC in both hard switch and resonant topologies
- Welding



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STGW40NC60WD	GW40NC60WD	TO-247	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GS} = 0$)	600	V
$I_C^{(1)}$	Collector current (continuous) at 25°C	70	A
$I_C^{(1)}$	Collector current (continuous) at 100°C	40	A
$I_{CL}^{(2)}$	Turn-off SOA minimum current	230	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Diode RMS forward current at $T_C=25^\circ\text{C}$	15	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	250	W
T_{stg}	Operating junction temperature	- 55 to 150	°C
T_j	Storage temperature		
T_L	Maximum lead temperature for soldering purpose (1.6mm from case, for 10sec.)	300	°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C) \cdot I_C}$$

2. $V_{clamp} = 480\text{V}$, $T_j = 150^\circ\text{C}$, $R_G = 10\Omega$, $V_{GE} = 15\text{V}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case Max	0.6	°C/W
Rthj-amb	Thermal resistance junction-ambient Max	50	°C/W

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-emitter breakdown voltage	$I_C = 1\text{mA}, V_{GE} = 0$	600			V
$V_{CE(SAT)}$	Collector-emitter saturation voltage	$V_{GE}= 15\text{V}, I_C= 30\text{A}, T_j= 25^{\circ}\text{C}$ $V_{GE}= 15\text{V}, I_C= 30\text{A}, T_j= 125^{\circ}\text{C}$		2.1 1.9	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE}= V_{GE}, I_C= 250\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \text{Max rating}, T_c=25^{\circ}\text{C}$ $V_{GE} = \text{Max rating}, T_c=125^{\circ}\text{C}$			50 3	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{V}, V_{CE} = 0$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{V}, I_C= 30\text{A}$		20		S

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{V}, f = 1\text{MHz}, V_{GE} = 0$		2900		pF
C_{oes}	Output capacitance			298		pF
C_{res}	Reverse transfer capacitance			59		pF
Q_g	Total gate charge	$V_{CE} = 390\text{V}, I_C = 30\text{A},$ $V_{GE} = 15\text{V},$ <i>(see Figure 16)</i>		126		nC
Q_{ge}	Gate-emitter charge			16		nC
Q_{gc}	Gate-collector charge			46		nC
I_{CL}	Turn-off SOA Minimum current	$V_{clamp} = 480\text{V}, T_j = 150^{\circ}\text{C}$ $R_G = 10\Omega, V_{GE} = 15\text{V}$		230		A

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390V, I_C = 30A$		33		ns
t_r	Current rise time	$R_G = 10\Omega, V_{GE} = 15V,$		12		ns
$(di/dt)_{on}$	Turn-on current slope	$T_J = 25^\circ C$ (see Figure 15)		260		A/ μs
$t_{d(on)}$	Turn-on delay timeE	$V_{CC} = 390V, I_C = 30A$		32		ns
t_r	Current rise time	$R_G = 10\Omega, V_{GE} = 15V,$		14		ns
$(di/dt)_{on}$	Turn-on current slope	$T_J = 125^\circ C$ (see Figure 15)		2300		A/ μs
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390V, I_C = 30A,$		26		ns
$t_{d(off)}$	Turn-off delay time	$R_{GE} = 10\Omega, V_{GE} = 15V,$		168		ns
t_f	Current fall time	$T_J = 25^\circ C$ (see Figure 15)		36		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390V, I_C = 30A,$		54		ns
$t_{d(off)}$	Turn-off delay time	$R_{GE} = 10\Omega, V_{GE} = 15V,$		213		ns
t_f	Current fall time	$T_J = 125^\circ C$ (see Figure 15)		67		ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390V, I_C = 30A$		302		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10\Omega, V_{GE} = 15V,$		394		μJ
E_{ts}	Total switching losses	$T_J = 25^\circ C$ (see Figure 15)		651		μJ
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390V, I_C = 30A$		553		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10\Omega, V_{GE} = 15V,$		750		μJ
E_{ts}	Total switching losses	$T_J = 125^\circ C$ (see Figure 15)		1303		μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2 E_{on} include diode recovery energy. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

Table 7. Collector-emitter diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
V_f	Forward on-voltage	$I_f = 3.5A$ $I_f = 3.5A, T_j = 125^\circ C$		1.4	1.9	V
				1.1		V
t_{rr}	Reverse recovery time	$I_f = 20A, V_R = 40V,$ $T_j = 25^\circ C, di/dt = 100A/\mu s$ <i>(see Figure 18)</i>		45		ns
Q_{rr}	Reverse recovery charge			56		nC
I_{rrm}	Reverse recovery current			2.5		A
t_{rr}	Reverse recovery time	$I_f = 20A, V_R = 40V,$ $di/dt = 100A/\mu s,$ $T_j = 125^\circ C$ <i>(see Figure 18)</i>		100		ns
Q_{rr}	Reverse recovery charge			290		nC
I_{rrm}	Reverse recovery current			5.8		A

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

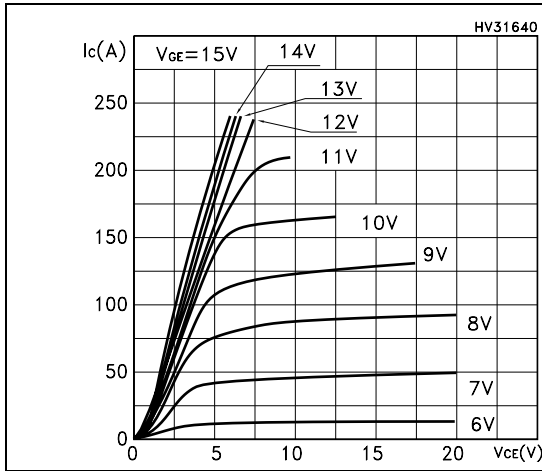


Figure 2. Transfer characteristics

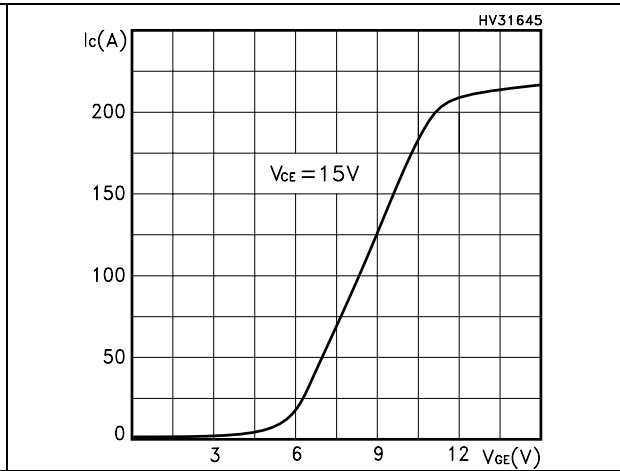


Figure 3. Transconductance

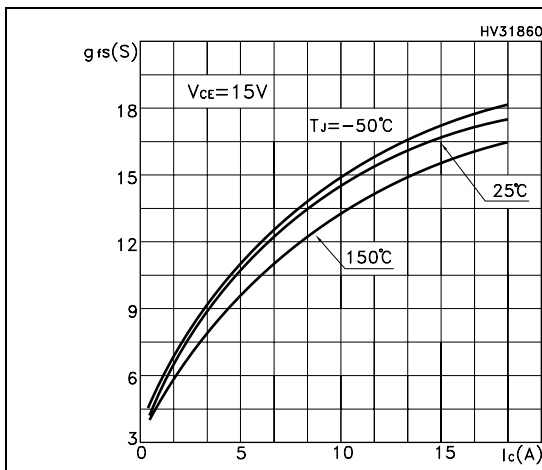


Figure 4. Collector-emitter on voltage vs temperature

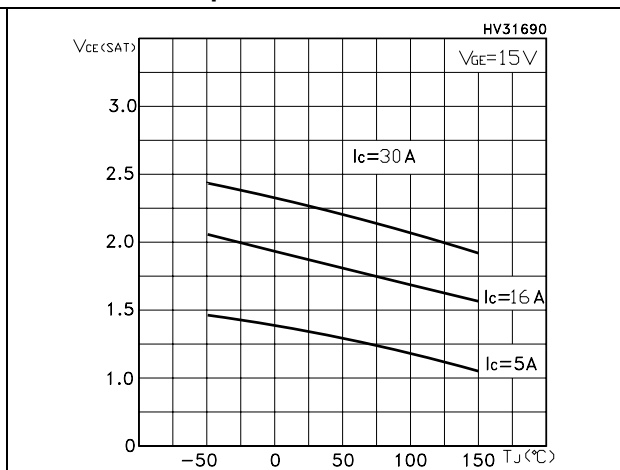


Figure 5. Collector-emitter on voltage vs collector current

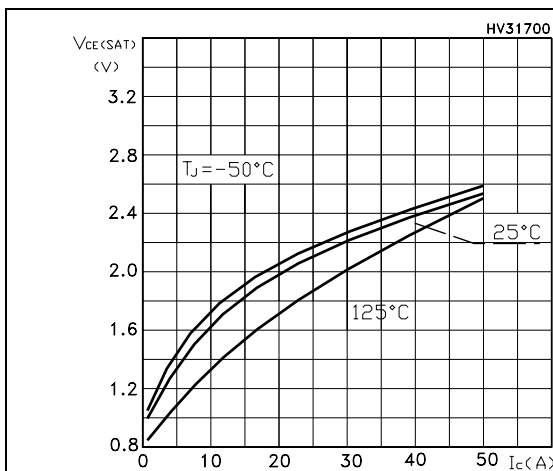


Figure 6. Normalized gate threshold vs temperature

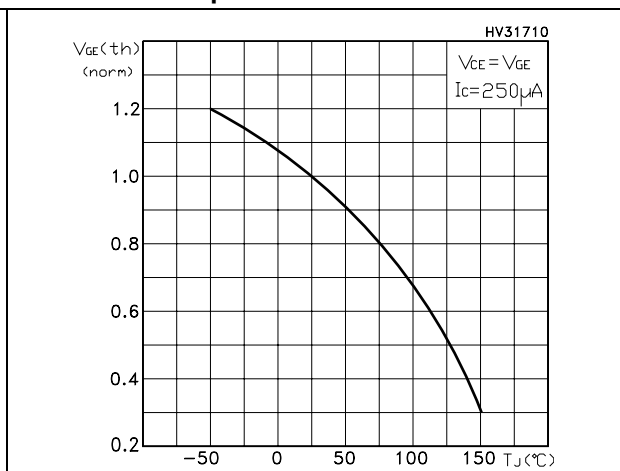


Figure 7. Normalized breakdown voltage vs temperature

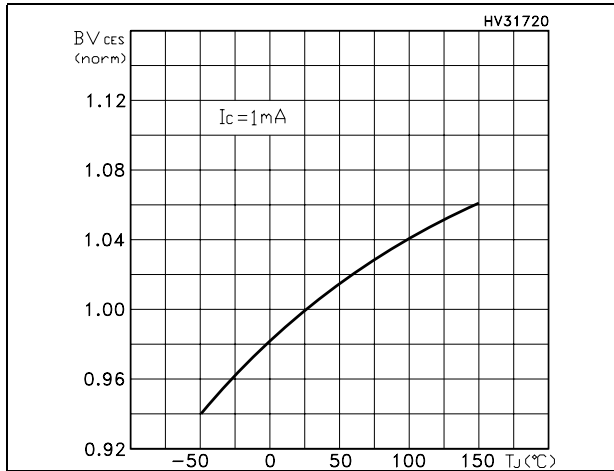


Figure 8. Gate charge vs gate-emitter voltage

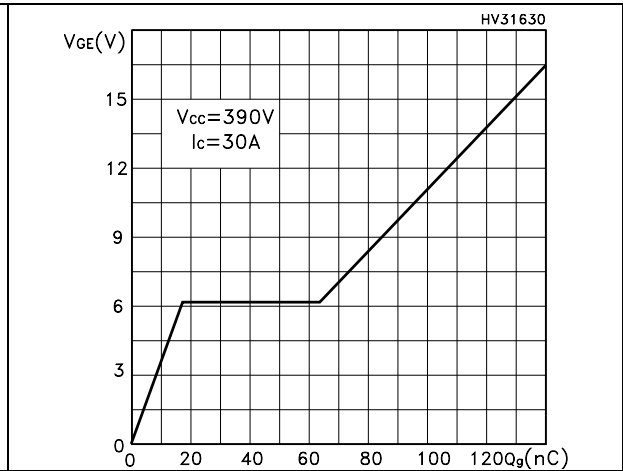


Figure 9. Capacitance variations

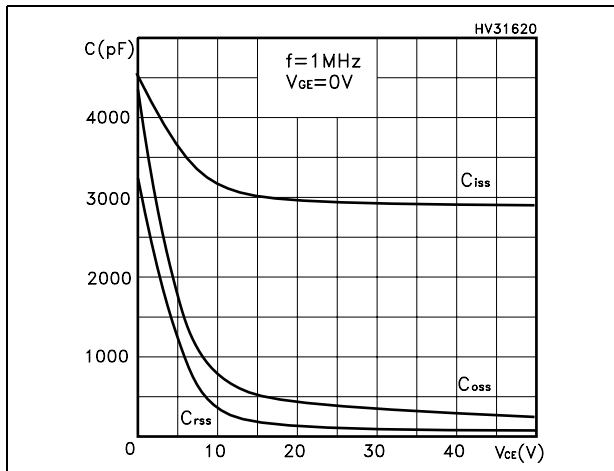


Figure 10. Switching losses vs temperature

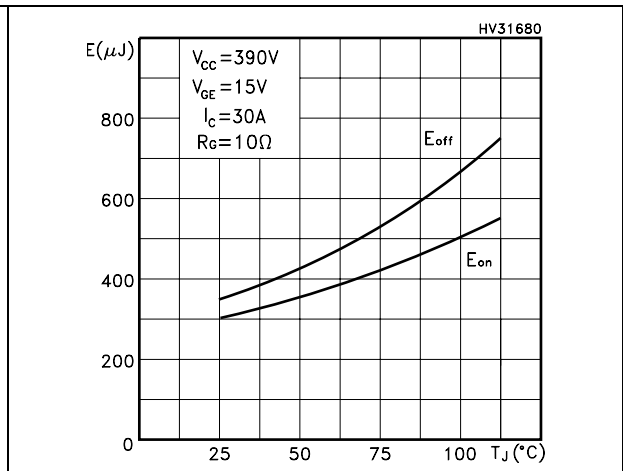


Figure 11. Switching losses vs gate resistance

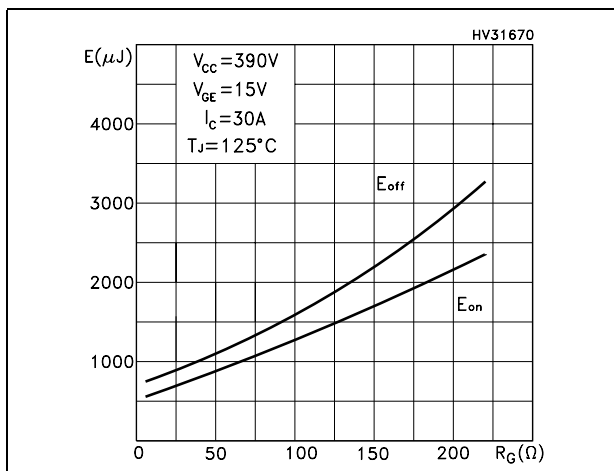


Figure 12. Switching losses vs collector current

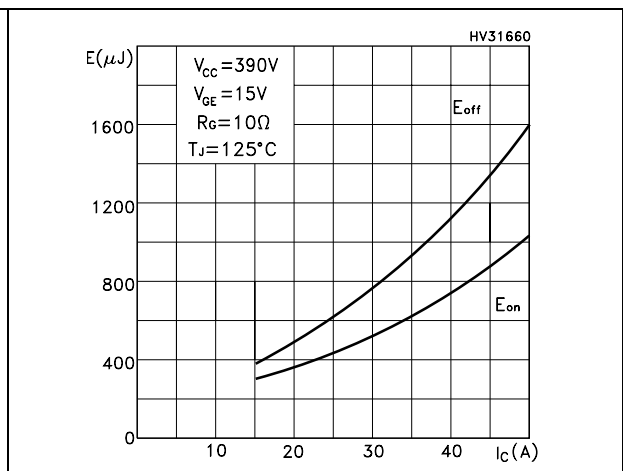
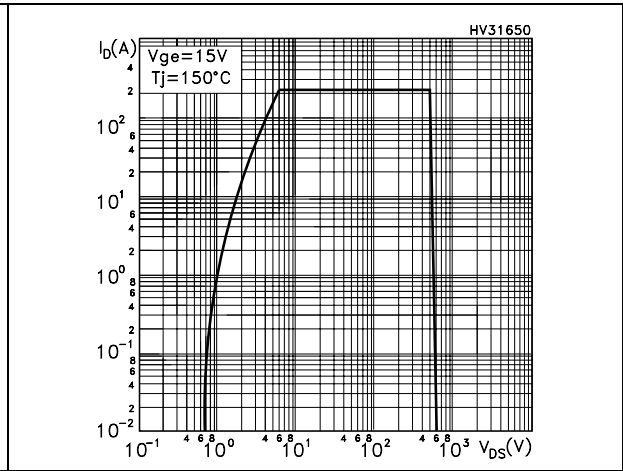
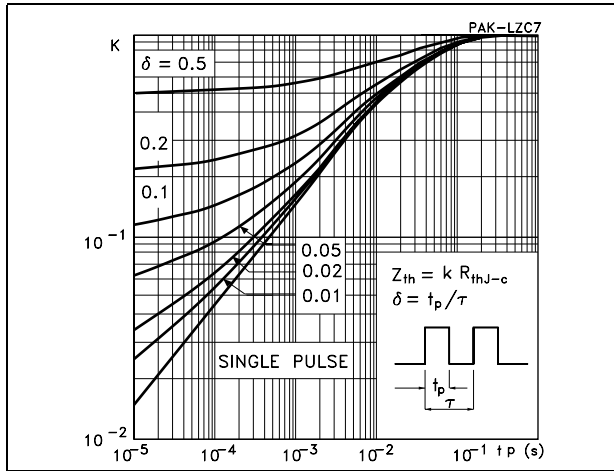


Figure 13. Thermal impedance

Figure 14. Turn-off SOA



3 Test circuit

Figure 15. Test circuit for inductive load switching

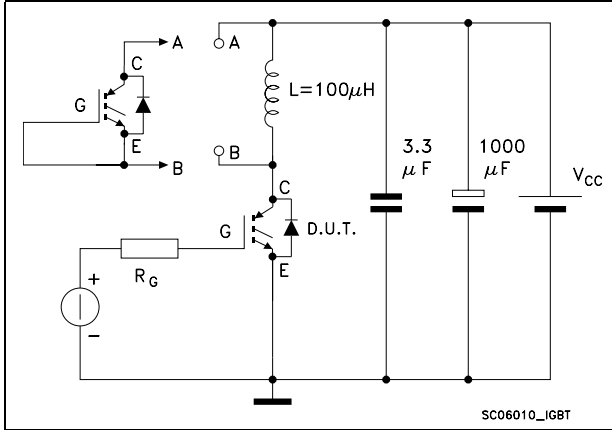


Figure 16. Gate charge test circuit

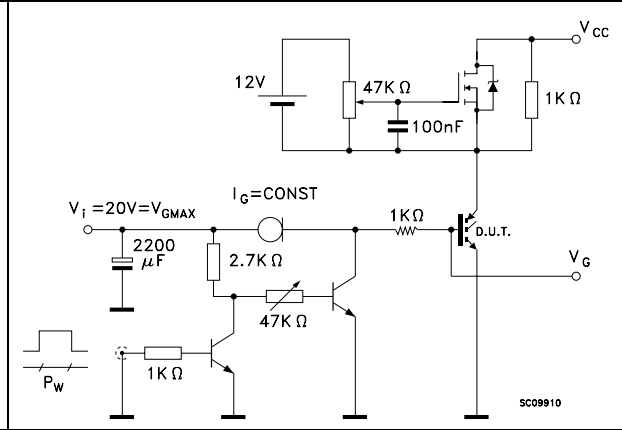


Figure 17. Switching waveforms

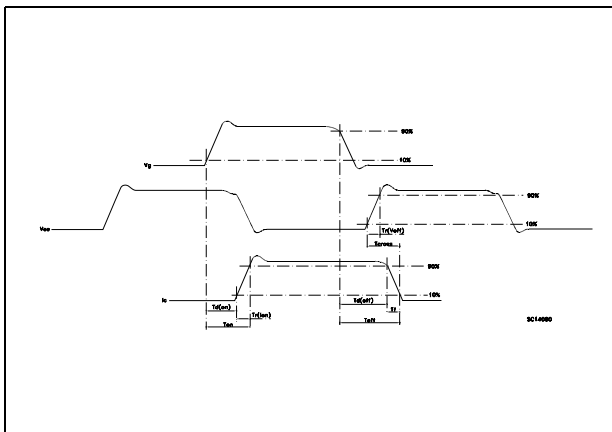
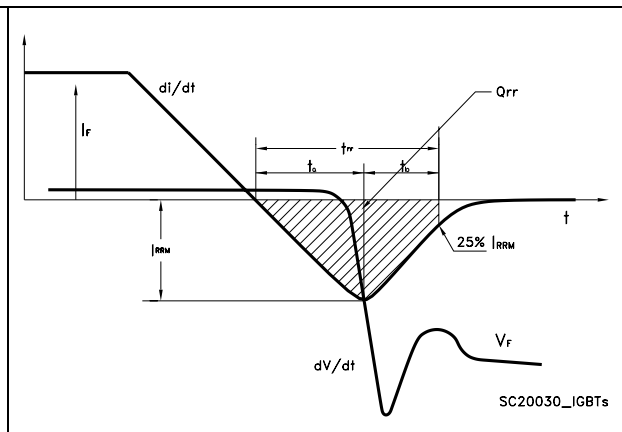


Figure 18. Diode recovery times waveform

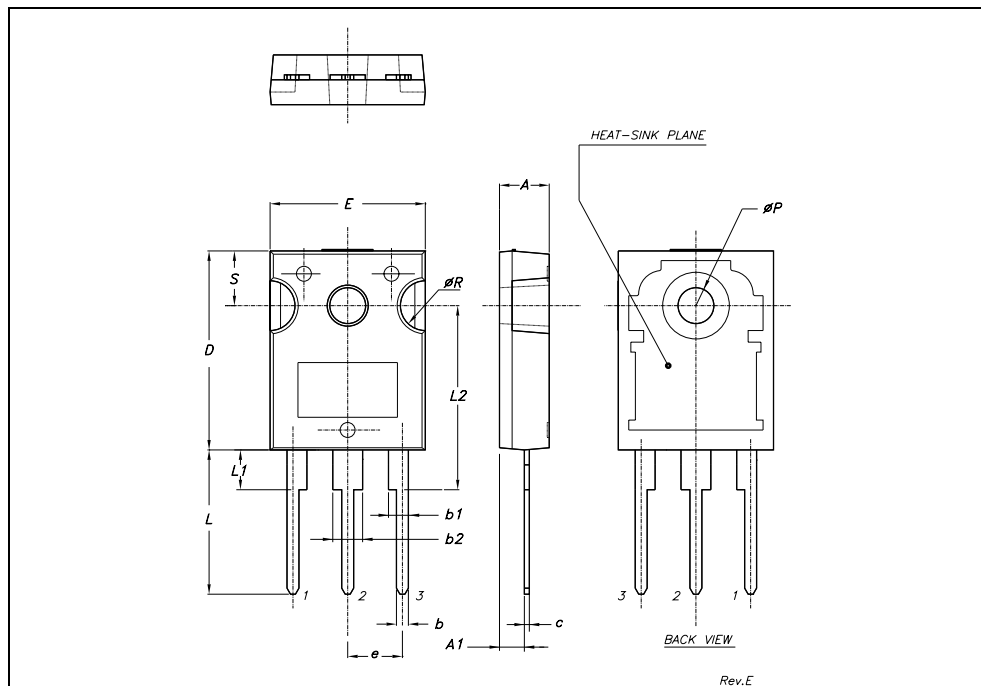


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



5 Revision history

Table 8. Revision history

Date	Revision	Changes
8-Jun-2006	1	First release
10-Jul-2006	2	Modified <i>Dynamic</i>

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